

DATA SHEET

BUJ403A

Silicon Diffused Power Transistor

Product specification

October 2018

Silicon Diffused Power Transistor

BUJ403A

GENERAL DESCRIPTION

High-voltage, high-speed planar-passivated npn power switching transistor in TO220AB envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

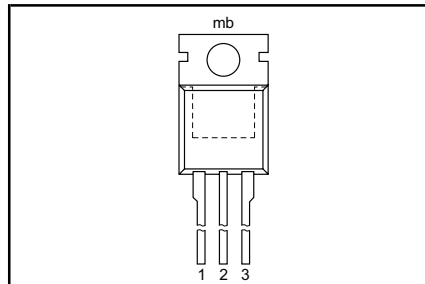
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|-------------|---------------------------------------|---|------|------|------|
| V_{CESM} | Collector-emitter voltage peak value | $V_{BE} = 0\text{ V}$ | - | 1200 | V |
| V_{CBO} | Collector-Base voltage (open emitter) | | - | 1200 | V |
| V_{CEO} | Collector-emitter voltage (open base) | | - | 550 | V |
| I_C | Collector current (DC) | | - | 6 | A |
| I_{CM} | Collector current peak value | | - | 10 | A |
| P_{tot} | Total power dissipation | $T_{mb} \leq 25\text{ °C}$ | - | 100 | W |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C = 2\text{ A}; I_B = 0.4\text{ A}$ | 0.15 | 1.0 | V |
| h_{FEsat} | DC current gain | $I_C = 3\text{ A}; V_{CE} = 5\text{ V}$ | 15.5 | - | |
| t_f | Fall time | $I_C = 2.5\text{ A}; I_{B1} = 0.5\text{ A}$ | 170 | 300 | ns |

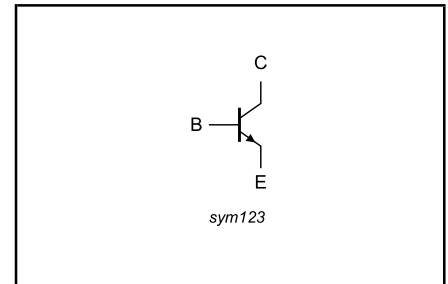
PINNING - TO220AB

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | collector |
| 3 | emitter |
| tab | collector |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------|--|----------------------------|------|------|------|
| V_{CESM} | Collector to emitter voltage | $V_{BE} = 0\text{ V}$ | - | 1200 | V |
| V_{CEO} | Collector to emitter voltage (open base) | | - | 550 | V |
| V_{CBO} | Collector to base voltage (open emitter) | | - | 1200 | V |
| I_C | Collector current (DC) | | - | 6 | A |
| I_{CM} | Collector current peak value | | - | 10 | A |
| I_B | Base current (DC) | | - | 3 | A |
| I_{BM} | Base current peak value | | - | 5 | A |
| P_{tot} | Total power dissipation | $T_{mb} \leq 25\text{ °C}$ | - | 100 | W |
| T_{stg} | Storage temperature | | -65 | 150 | °C |
| T_j | Junction temperature | | - | 150 | °C |

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------------|---------------------------|-------------|------|------|------|
| $R_{th\ j-mb}$ | Junction to mounting base | | - | 1.25 | K/W |
| $R_{th\ j-a}$ | Junction to ambient | in free air | 60 | - | K/W |

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BUJ403A

STATIC CHARACTERISTICS

 $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------------|--|--|------|------|------|------|
| I_{CES}, I_{CBO} | Collector cut-off current ¹ | $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ | - | - | 1.0 | mA |
| I_{CES} | | $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$ | - | - | 2.0 | mA |
| I_{CEO} | Collector cut-off current ¹ | $V_{CEO} = V_{CEOMmax} (550\text{ V})$ | - | - | 0.1 | mA |
| I_{EBO} | Emitter cut-off current | $V_{EB} = 7\text{ V}; I_C = 0\text{ A}$ | - | - | 0.1 | mA |
| $V_{CEOsust}$ | Collector-emitter sustaining voltage | $I_B = 0\text{ A}; I_C = 10\text{ mA};$ $L = 25\text{ mH}$ | 550 | - | - | V |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C = 2.0\text{ A}; I_B = 0.4\text{ A}$ | - | 0.15 | 1.0 | V |
| V_{BEsat} | Base-emitter saturation voltage | $I_C = 2.0\text{ A}; I_B = 0.4\text{ A}$ | - | 0.91 | 1.5 | V |
| h_{FE} | DC current gain | $I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$ | 13 | 25 | - | |
| h_{FE} | DC current gain | $I_C = 500\text{ mA}; V_{CE} = 5\text{ V}$ | 20 | 30 | 47 | |
| h_{FEsat} | | $I_C = 2.0\text{ A}; V_{CE} = 5\text{ V}$ | 13 | 18.5 | 25 | |
| h_{FEsat} | | $I_C = 3.0\text{ A}; V_{CE} = 5\text{ V}$ | - | 15.5 | - | |

DYNAMIC CHARACTERISTICS

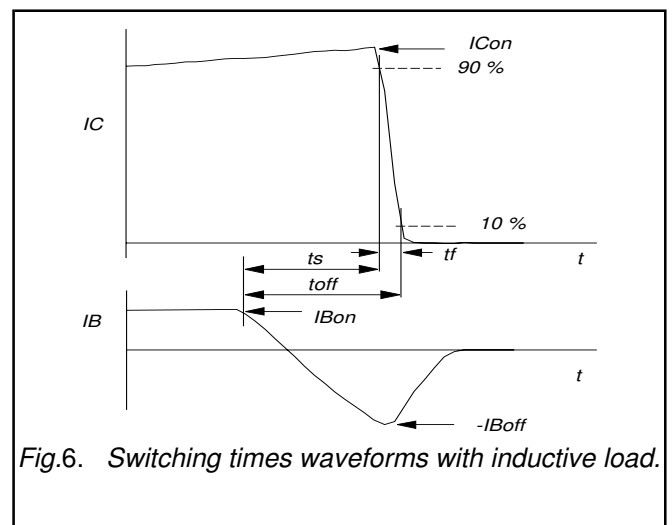
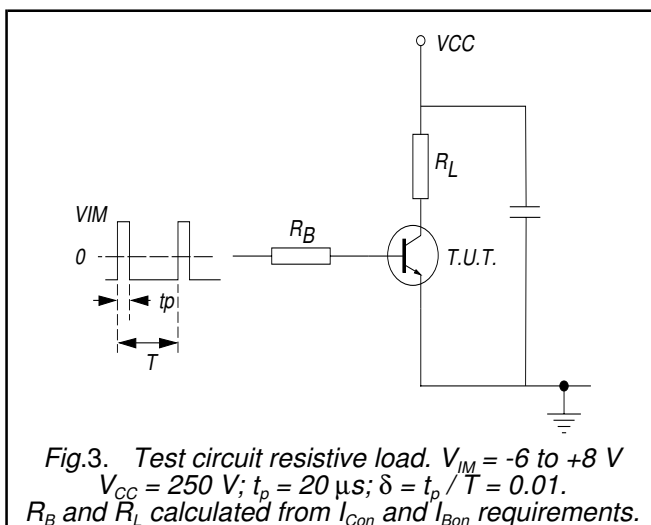
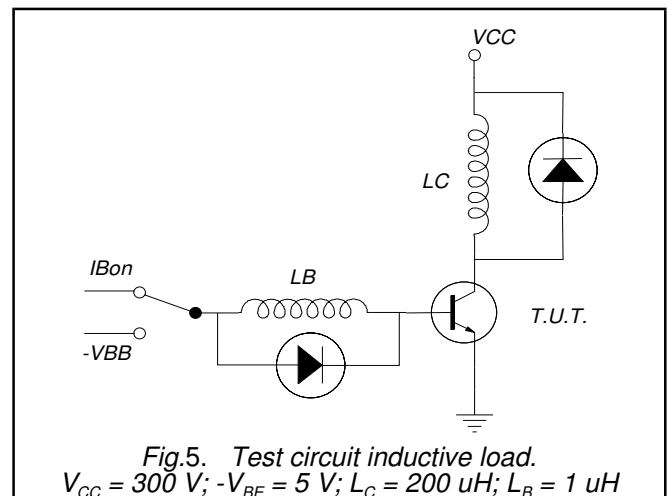
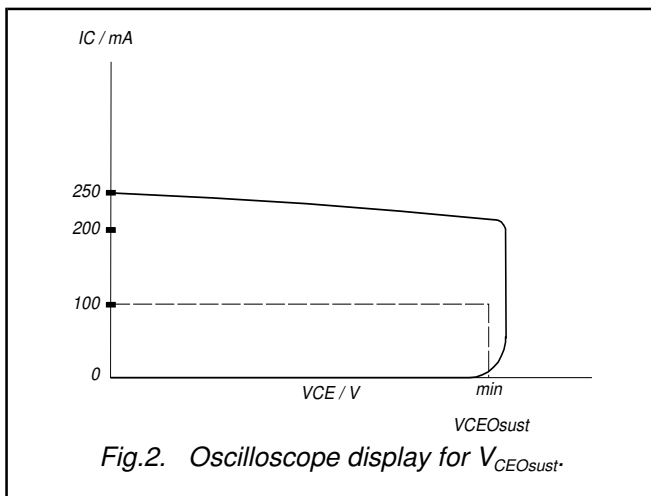
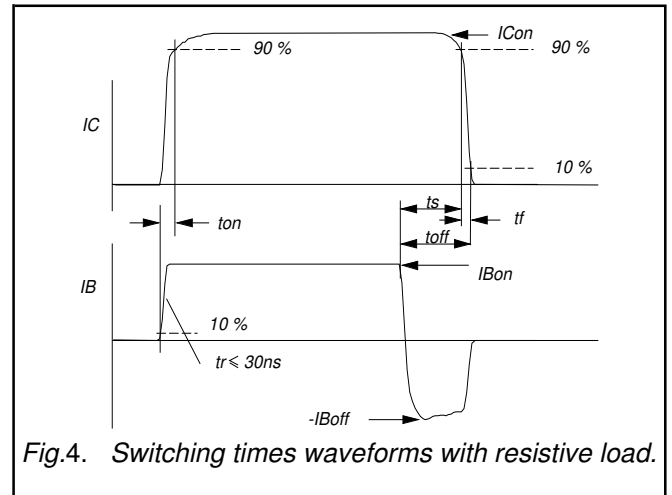
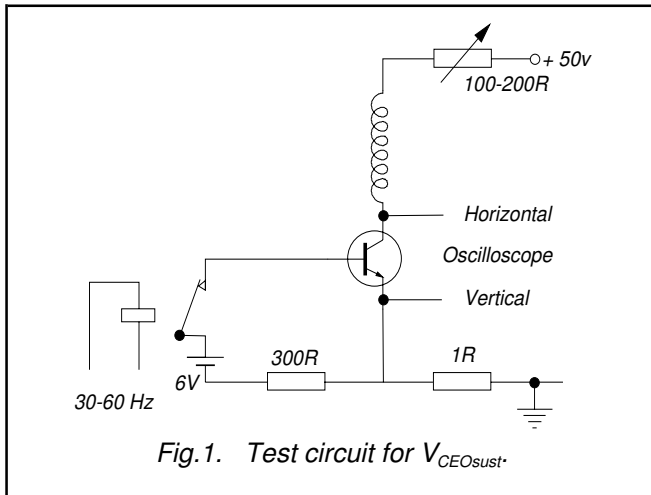
 $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------|----------------------------------|--|------|------|---------------|
| | Switching times (resistive load) | $I_{Con} = 2.5\text{ A}; I_{Bon} = -I_{Boff} = 0.5\text{ A};$ $R_L = 75\text{ ohms}; V_{BB2} = 4\text{ V};$ | | | |
| t_{on} | Turn-on time | | - | 0.5 | μs |
| t_s | Turn-off storage time | | - | 3 | μs |
| t_f | Turn-off fall time | | - | 0.3 | μs |
| | Switching times (inductive load) | $I_{Con} = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}$ | | | |
| t_s | Turn-off storage time | | - | 1.5 | μs |
| t_f | Turn-off fall time | | 170 | 300 | ns |
| | Switching times (inductive load) | $I_{Con} = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}; T_j = 100\text{ }^{\circ}\text{C}$ | | | |
| t_s | Turn-off storage time | | - | 1.8 | μs |
| t_f | Turn-off fall time | | - | 300 | ns |

¹ Measured with half sine-wave voltage (curve tracer).

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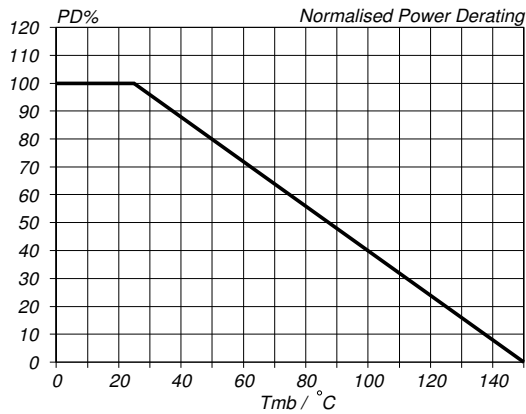


Fig. 7. Normalised power dissipation.
 $PD\% = 100 \cdot PD / PD_{25^\circ C} = f(T_{mb})$

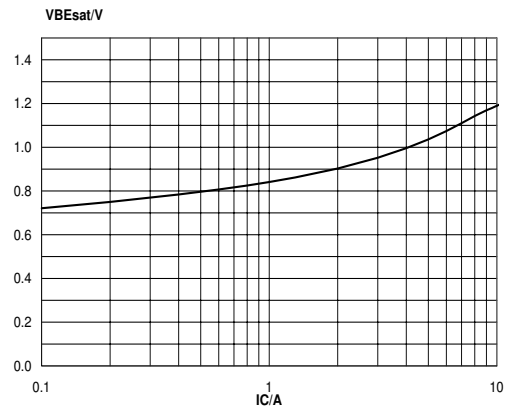


Fig. 10. Base-Emitter saturation voltage.
 Solid lines = typ values, $V_{BEsat} = f(I_C)$; at $I_C/I_B = 4$.

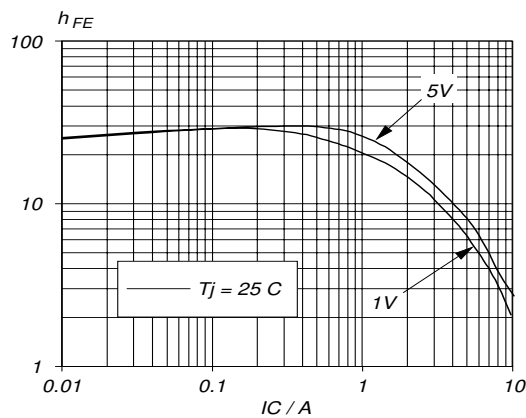


Fig. 8. Typical DC current gain. $h_{FE} = f(I_C)$
 parameter V_{CE}

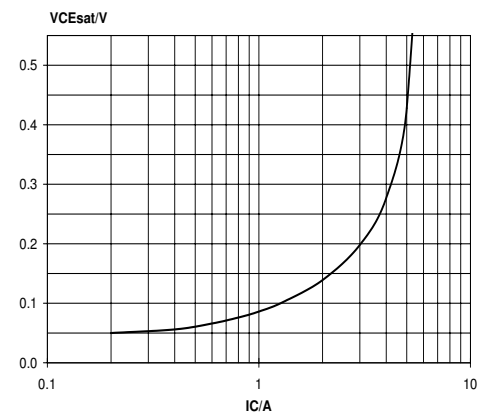


Fig. 11. Collector-Emitter saturation voltage.
 Solid lines = typ values, $V_{CEsat} = f(I_C)$; at $I_C/I_B = 4$.

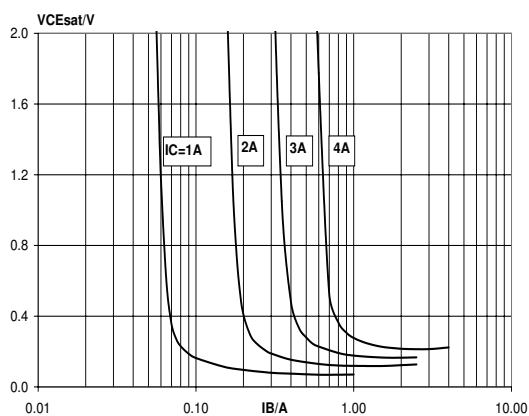


Fig. 9. Collector-Emitter saturation voltage.
 Solid lines = typ values, $V_{CEsat} = f(I_B)$; $T_J = 25^\circ C$.

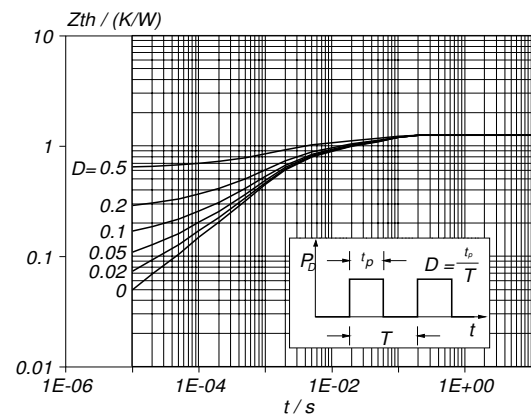


Fig. 12. Transient thermal impedance.
 $Z_{th j-mb} = f(t)$; parameter $D = t_p / T$

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BUJ403A

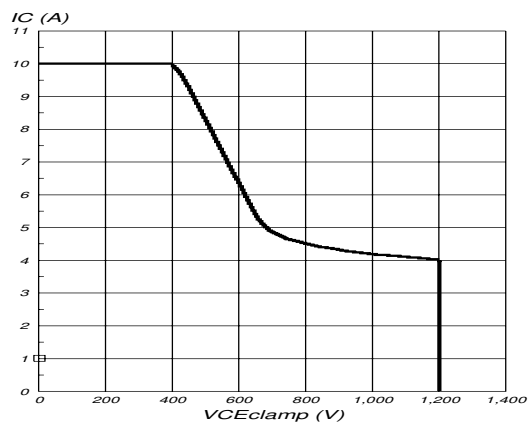


Fig.13. Reverse bias safe operating area $T_j \leq T_{jmax}$

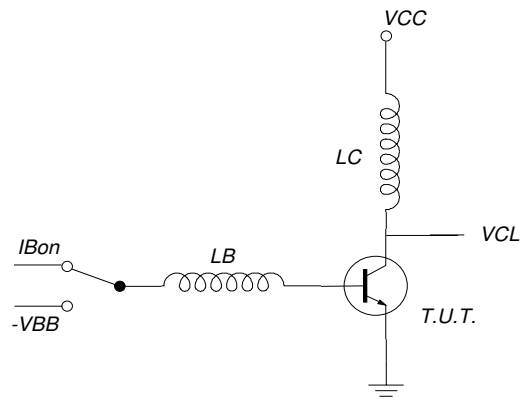


Fig.14. Test Circuit for reverse bias safe operating area
 $V_{cl} \leq 1000V$; $V_{cc} = 150V$; $V_{BB} = -5V$; $L_B = 1\mu H$; $L_c = 200\mu H$

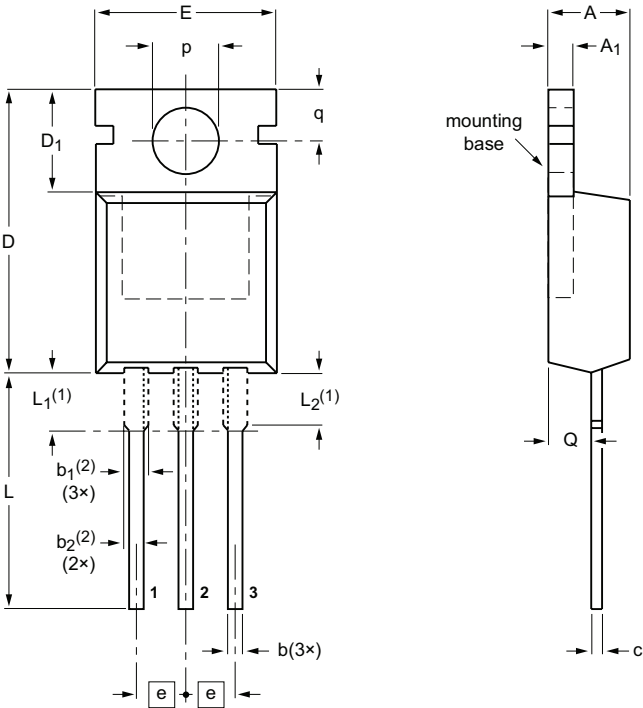
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MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78




DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | b | b ₁ (2) | b ₂ (2) | c | D | D ₁ | E | e | L | L ₁ (1) | L ₂ (1) max. | p | q | Q |
|------|------------|----------------|------------|--------------------|--------------------|------------|--------------|----------------|-------------|------|--------------|--------------------|----------------------------|------------|------------|------------|
| mm | 4.7 4.1 | 1.40 1.25 | 0.9 0.6 | 1.6 1.0 | 1.3 1.0 | 0.7 0.4 | 16.0 15.2 | 6.6 5.9 | 10.3 9.7 | 2.54 | 15.0 12.8 | 3.30 2.79 | 3.0 | 3.8 3.5 | 3.0 2.7 | 2.6 2.2 |

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|-----------------|-------|--|---|----------------------|
| | IEC | JEDEC | JEITA | | | |
| SOT78 | | 3-lead TO-220AB | SC-46 | |  | 08-04-23 08-06-13 |

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|--------------------------------|--------------------|---|
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